Quad 2-Channel Analog Multiplexer/Demultiplexer

The MC14551B is a digitally–controlled analog switch. This device implements a 4PDT solid state switch with low ON impedance and very low OFF Leakage current. Control of analog signals up to the complete supply voltage range can be achieved.

- Triple Diode Protection on All Control Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Analog Voltage Range (V_{DD} V_{EE}) = 3.0 to 18 V
 Note: V_{EE} must be ≤ V_{SS}
- Linearized Transfer Characteristics
- Low Noise $12 \text{ nV}\sqrt{\text{Cycle}}$, $f \ge 1.0 \text{ kHz typical}$
- For Low R_{ON}, Use The HC4051, HC4052, or HC4053 High–Speed CMOS Devices
- Switch Function is Break Before Make

MAXIMUM RATINGS (2.)

Symbol	Parameter	Value	Unit
V _{DD}	DC Supply Voltage Range (Referenced to V _{EE} , V _{SS} ≥ V _{EE})	- 0.5 to + 18.0	V
V _{in} , V _{out}	Input or Output Voltage (DC or Transient) (Referenced to V _{SS} for Control Input & V _{EE} for Switch I/O)	- 0.5 to V _{DD} + 0.5	V
I _{in}	Input Current (DC or Transient), per Control Pin	± 10	mA
I _{sw}	Switch Through Current	± 25	mA
P _D	Power Dissipation, per Package (3.)	500	mW
T _A	Ambient Temperature Range	- 55 to + 125	°C
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

- Maximum Ratings are those values beyond which damage to the device may occur.
- Temperature Derating: Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ for control inputs and $V_{EE} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ for Switch I/O.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} , V_{EE} or V_{DD}). Unused outputs must be left open.



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MARKING DIAGRAMS

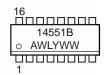


PDIP-16 P SUFFIX CASE 648



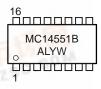


SOIC-16 D SUFFIX CASE 751B





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week

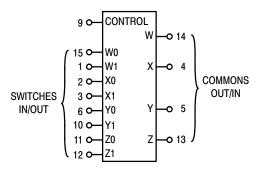
ORDERING INFORMATION

Device	Package	Shipping Shipping
MC14551BCP	PDIP-16	2000/Box
MC14551BD	SOIC-16	48/Rail
MC14551BDR2	SOIC-16	2500/Tape & Reel
MC14551BF	SOEIAJ-16	See Note 1.

 For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

PIN ASSIGNMENT

W1 [1 •	16] V _{DD}
X0 [2	15] W0
X1 [3	14] W
Χ [4	13] z
Υ [5	12] Z1
Y0 [6	11] Z0
V _{EE} [7	10] Y1
v _{ss} [8	9	CONTROL



 V_{DD} = Pin 16 V_{SS} = Pin 8 V_{EE} = Pin 7

Control	ON				
0	W0 X0 Y0 Z0				
1	W1 X1 Y1 Z1				

NOTE: Control Input referenced to V_{SS}, Analog Inputs and Outputs reference to V_{EE}. V_{EE} must be \leq V_{SS}.

ELECTRICAL CHARACTERISTICS

	1			- 5	5°C		25°C		12	5°C	
Characteristic	Symbol	V_{DD}	Test Conditions	Min	Max	Min	Typ ^(4.)	Max	Min	Max	Unit
SUPPLY REQUIREMENTS	(Voltages R	eferen	ced to V _{EE})								
Power Supply Voltage Range	V _{DD}	_	$V_{DD} - 3.0 \ge V_{SS} \ge V_{EE}$	3.0	18	3.0	_	18	3.0	18	V
Quiescent Current Per Package	I _{DD}	5.0 10 15			5.0 10 20	_ _ _	0.005 0.010 0.015	5.0 10 20		150 300 600	μА
Total Supply Current (Dynamic Plus Quiescent, Per Package)	I _{D(AV)}	5.0 10 15	$T_A = 25^{\circ}\text{C only (The} \\ \text{channel component,} \\ (V_{in} - V_{out})/R_{on}, \text{ is} \\ \text{not included.)}$			Typical	(0.07 μΑ/ (0.20 μΑ/ (0.36 μΑ/	kHz) f +	I_{DD}		μА
CONTROL INPUT (Voltages	Reference	d to V _S	_(S)								
Low-Level Input Voltage	V _{IL}	5.0 10 15	R _{on} = per spec, I _{off} = per spec		1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0		1.5 3.0 4.0	V
High-Level Input Voltage	V _{IH}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	3.5 7.0 11	_	3.5 7.0 11	2.75 5.50 8.25	_ _ _	3.5 7.0 11	_ _ _	V
Input Leakage Current	I _{in}	15	V _{in} = 0 or V _{DD}	_	±0.1	_	±0.00001	±0.1	_	±1.0	μΑ
Input Capacitance	C _{in}	_		_	_	_	5.0	7.5	_		pF
SWITCHES IN/OUT AND CO	OMMONS (OUT/IN	I — W, X, Y, Z (Voltages R	eferen	ced to V	'EE)					
Recommended Peak-to- Peak Voltage Into or Out of the Switch	V _{I/O}	_	Channel On or Off	0	V _{DD}	0	_	V _{DD}	0	V _{DD}	V _{p-p}
Recommended Static or Dynamic Voltage Across the Switch ^(5.) (Figure 3)	ΔV_{switch}	-	Channel On	0	600	0	_	600	0	300	mV
Output Offset Voltage	Voo	_	V _{in} = 0 V, No Load	_	_	_	10	_	_	_	μV
ON Resistance	R _{on}	5.0 10 15	$\begin{array}{l} \Delta V_{Switch} \leq 500 \text{ mV} \ ^{(5.)}, \\ V_{in} = V_{IL} \text{ or } V_{IH} \\ \text{ (Control), and } V_{in} = \\ 0 \text{ to } V_{DD} \text{ (Switch)} \end{array}$	_	800 400 220	_ _ _	250 120 80	1050 500 280		1200 520 300	Ω
ΔON Resistance Between Any Two Channels in the Same Package	ΔR_{on}	5.0 10 15		_ _ _	70 50 45	_ _ _	25 10 10	70 50 45	_ _ _	135 95 65	Ω
Off-Channel Leakage Current (Figure 8)	l _{off}	15	V _{in} = V _{IL} or V _{IH} (Control) Channel to Channel or Any One Channel	_	±100	_	±0.05	±100	_	±1000	nA
Capacitance, Switch I/O	C _{I/O}	_	Switch Off	_		_	10				pF
Capacitance, Common O/I	C _{O/I}	_		_	_	_	17	_	_	_	pF
Capacitance, Feedthrough (Channel Off)	C _{I/O}		Pins Not Adjacent Pins Adjacent				0.15 0.47				pF

Data labeled "Typ" is not to be used for design purposes, but is intended as an indication of the IC's potential performance.
 For voltage drops across the switch (ΔV_{switch}) > 600 mV (> 300 mV at high temperature), excessive V_{DD} current may be drawn; i.e. the current out of the switch may contain both V_{DD} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, $T_A = 25^{\circ}C$, $V_{EE} \leq V_{SS}$)

Characteristic	Symbol	V _{DD} – V _{EE} Vdc	Min	Тур ^(6.)	Max	Unit
Propagation Delay Times Switch Input to Switch Output (R _L = 10 k Ω) t_{PLH} , t_{PHL} = (0.17 ns/pF) C _L + 26.5 ns	t _{PLH} , t _{PHL}	5.0	_	35	90	ns
t_{PLH} , t_{PHL} = (0.08 ns/pF) C_L + 11 ns t_{PLH} , t_{PHL} = (0.06 ns/pF) C_L + 9.0 ns		10 15	_	15 12	40 30	
Control Input to Output (R _L = 10 k Ω) V _{EE} = V _{SS} (Figure 4)	t _{PLH} , t _{PHL}	5.0 10 15	_ _ _	350 140 100	875 350 250	ns
Second Harmonic Distortion $R_L = 10 \text{ k}\Omega, f = 1 \text{ kHz}, V_{in} = 5 \text{ V}_{p-p}$	_	10	_	0.07	_	%
Bandwidth (Figure 5) $R_L = 1 \text{ k}\Omega$, $V_{in} = 1/2 (V_{DD} - V_{EE})_{p-p}$, $20 \text{ Log} (V_{out}/V_{in}) = -3 \text{ dB}$, $C_L = 50 \text{ pF}$	BW	10	_	17	_	MHz
Off Channel Feedthrough Attenuation, Figure 5 $R_L = 1 \text{ k}\Omega$, $V_{in} = 1/2 \text{ (V}_{DD} - V_{EE})_{p-p}$, $f_{in} = 55 \text{ MHz}$	_	10	_	- 50	_	dB
Channel Separation (Figure 6) $R_L = 1 \ k\Omega, \ V_{in} = 1/2 \ (V_{DD} - V_{EE}) \ _{p-p}, \\ f_{in} = 3 \ MHz$	_	10	_	- 50	_	dB
Crosstalk, Control Input to Common O/I, Figure 7 R1 = 1 k Ω , R _L = 10 k Ω , Control t _r = t _f = 20 ns	_	10	_	75	_	mV

^{6.} Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

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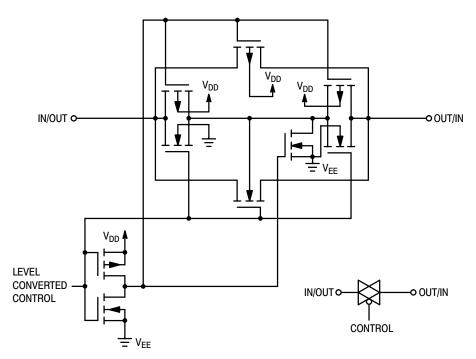


Figure 1. Switch Circuit Schematic

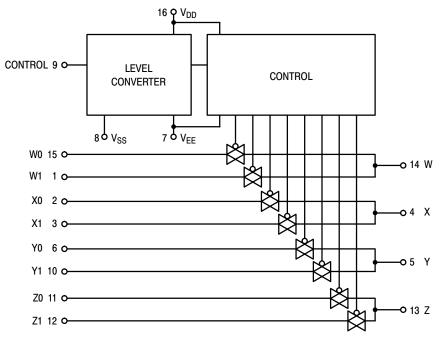


Figure 2. MC14551B Functional Diagram

TEST CIRCUITS

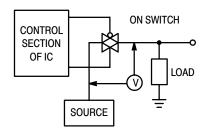


Figure 3. ΔV Across Switch

Control input used to turn ON or OFF the switch under test.

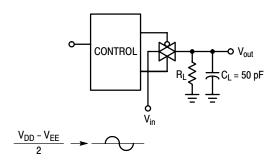


Figure 5. Bandwidth and Off-Channel Feedthrough Attenuation

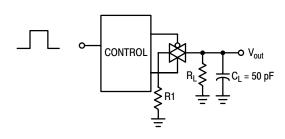


Figure 7. Crosstalk, Control Input to Common O/I

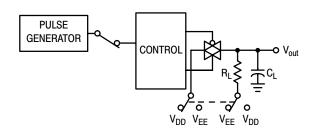


Figure 4. Propagation Delay Times, Control to Output

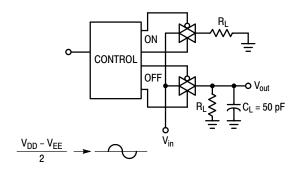


Figure 6. Channel Separation (Adjacent Channels Used for Setup)

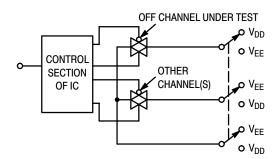


Figure 8. Off Channel Leakage

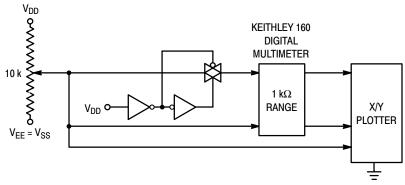


Figure 9. Channel Resistance (R_{ON}) Test Circuit

TYPICAL RESISTANCE CHARACTERISTICS

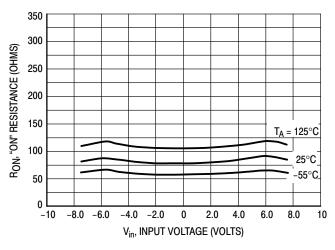


Figure 10. $V_{DD}\ @\ 7.5\ V,\ V_{EE}\ @\ -7.5\ V$

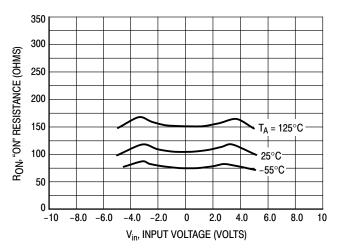


Figure 11. V_{DD} @ 5.0 V, V_{EE} @ - 5.0 V

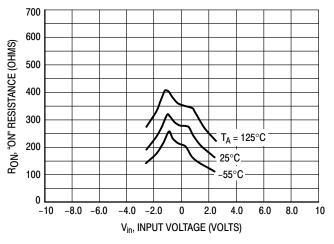


Figure 12. $\rm V_{DD} \ @ \ 2.5 \ V, \ V_{EE} \ @ \ -2.5 \ V$

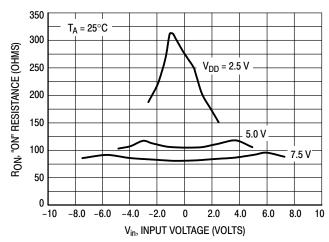


Figure 13. Comparison at 25°C, V_{DD} @ – V_{EE}

APPLICATIONS INFORMATION

Figure A illustrates use of the on-chip level converter detailed in Figure 2. The 0-to-5 volt Digital Control signal is used to directly control a 9 V_{p-p} analog signal.

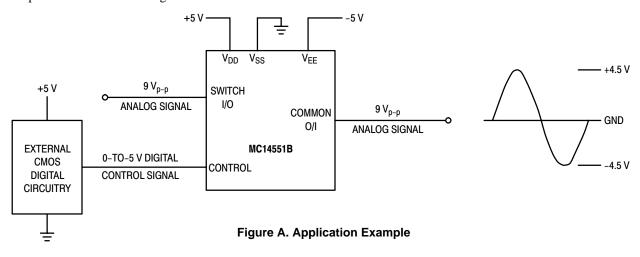
The digital control logic levels are determined by V_{DD} and V_{SS} . The V_{DD} voltage is the logic high voltage; the V_{SS} voltage is logic low. For the example, $V_{DD} = +5$ V = logic high at the control inputs; $V_{SS} = GND = 0$ V = logic low.

The maximum analog signal level is determined by V_{DD} and V_{EE} . The V_{DD} voltage determines the maximum recommended peak above V_{SS} . The V_{EE} voltage determines the maximum swing below V_{SS} . For the example, $V_{DD}-V_{SS}=5$ volt maximum swing above V_{SS} ; $V_{SS}-V_{EE}=5$ volt maximum swing below V_{SS} . The example shows a \pm 4.5 volt signal which allows a 1/2 volt

margin at each peak. If voltage transients above V_{DD} and/or below V_{EE} are anticipated on the analog channels, external diodes (D_x) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The absolute maximum potential difference between V_{DD} and V_{EE} is 18.0 volts. Most parameters are specified up to 15 volts which is the recommended maximum difference between V_{DD} and V_{EE} .

Balanced supplies are not required. However, V_{SS} must be greater than or equal to V_{EE} . For example, V_{DD} = + 10 volts, V_{SS} = + 5 volts, and V_{EE} = - 3 volts is acceptable. See the table below.



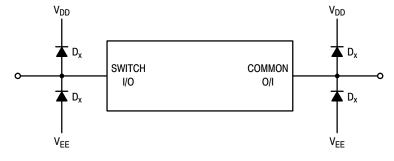


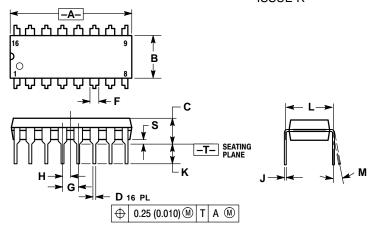
Figure B. External Schottky or Germanium Clipping Diodes

POSSIBLE SUPPLY CONNECTIONS

V _{DD} In Volts	V _{SS} In Volts	V _{EE} In Volts	Control Inputs Logic High/Logic Low In Volts	Maximum Analog Signal Range In Volts
+ 8	0	-8	+ 8/0	$+ 8 \text{ to} - 8 = 16 \text{ V}_{p-p}$
+ 5	0	- 12	+ 5/0	$+ 5 \text{ to} - 12 = 17 \text{ V}_{p-p}$
+ 5	0	0	+ 5/0	$+ 5 \text{ to } 0 = 5 \text{ V}_{p-p}$
+ 5	0	-5	+ 5/0	$+ 5 \text{ to } - 5 = 10 \text{ V}_{p-p}$
+ 10		- 5	+ 10/ + 5	$+ 10 \text{ to } - 5 = 15 \text{ V}_{p-p}$

PACKAGE DIMENSIONS

PDIP-16 **P SUFFIX** CASE 648-08 ISSUE R

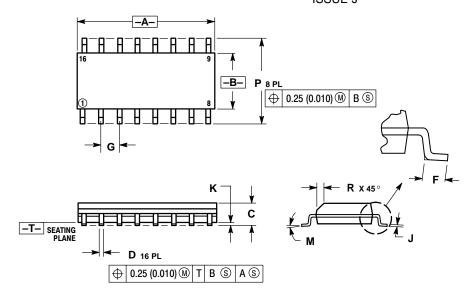


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	0.100 BSC		BSC
Н	0.050	BSC	1.27	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10 °	0°	10 °
S	0.020	0.040	0.51	1.01
	A B C D F G H J K L	DIM MIN A 0.740 B 0.250 C 0.145 F 0.040 G 0.100 H 0.050 J 0.008 K 0.110 L 0.295 M 0 °	A 0.740 0.770 B 0.250 0.270 C 0.145 0.175 D 0.015 0.021 F 0.040 0.70 G 0.100 BSC H 0.050 BSC J 0.008 0.015 K 0.110 0.130 L 0.295 0.305 M 0 ° 10°	DIM MIN MAX MIN A 0.740 0.770 18.80 B 0.250 0.270 6.35 C 0.145 0.175 3.69 D 0.015 0.021 0.39 F 0.040 0.70 1.02 G 0.100 BSC 2.54 H 0.050 BSC 1.27 J 0.008 0.015 0.21 K 0.110 0.130 2.80 L 0.295 0.305 7.50 M 0 ° 10 ° 0 °

PACKAGE DIMENSIONS

SOIC-16 **D SUFFIX** CASE 751B-05 ISSUE J

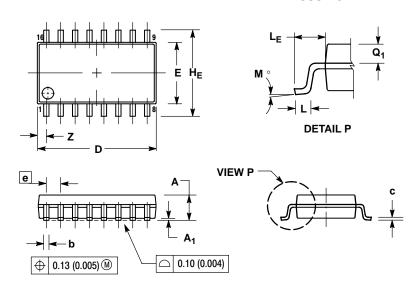


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** PLASTIC EIAJ SOIC PACKAGE CASE 966-01 **ISSUE O**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	1.27 BSC		BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031

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